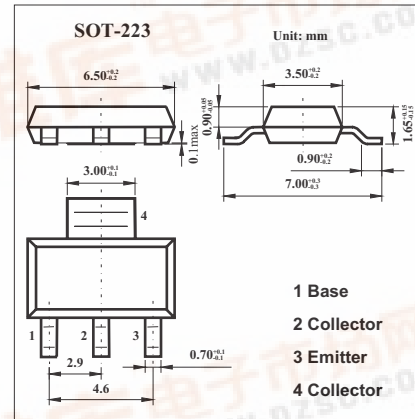


SMD Type Transistors

NPN Silicon Planar Medium Power Transistor
FZT657

■ Features

- Low saturation voltage



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	300	V
Collector-Emitter Voltage	V _{CEO}	300	V
Emitter-Base Voltage	V _{EBO}	5	V
Peak Pulse Current	I _{CM}	1	A
Continuous Collector Current	I _C	0.5	A
Power Dissipation at T _{amb} =25°C	P _{tot}	2	W
Operating and Storage Temperature Range	T _j :T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ.	Max	Unit
Collector-Base Breakdown Voltage	V _{(BR)CBO}	I _C =100μA	300			V
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C =10mA*	300			V
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	I _E =100μA	5			V
Collector Cut-Off Current	I _{CBO}	V _{CB} =200V			0.1	μA
Emitter Cut-Off Current	I _{EBO}	V _{EB} =3V			0.1	μA
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =100mA, I _B =10mA*			0.5	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _C =100mA, I _B =10mA*			1.0	V
Base-Emitter Turn-On Voltage	V _{BE(on)}	I _C =100mA, V _{CE} =5V*			1.0	V
Static Forward Current Transfer Ratio	h _{FE}	I _C =10mA, V _{CE} =5V*	40			
		I _C =100mA, V _{CE} =5V*	50			
Transition Frequency	f _T	I _C =10mA, V _{CE} =20V, f=20MHz	30			MHz
Output Capacitance	C _{obo}	V _{CB} =20V, f=1MHz			20	pF

* Measured under pulsed conditions. Pulse Width=300μs. Duty cycle≤2%

■ Marking

Marking	FZT657
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